





INFORMATION DISCLOSURE CITATION

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Applicant(s)

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*EXAMINER
INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"SOI waveguide GeSi avalanche pin photodetector at 1.3 um wavelength, Tomomi Yoshimoto et al., IEICE Trans. Electron, Vol. E81, No. 10, October 10, 1998, pages 1667-1669.

"High-speed metal-semiconductor-metal photodetectors fabricated on SOI-substrates, K. Honkanen et al., Physica Scripta, Vol. T79, 1999, pages 127-130.

"140-GHz metal-semiconductor-metal photodetectors on silicon-on-insulator substrate with a scaled active layer", M. Y. Liu et al., Appl. Phys. Lett. 65 (7), August 15, 1994.

"Comparison of the picosecond characteristics of silicon and silicon-on-sapphire metal-semiconductor-metal photodiodes", Chia-Chi Wang et al., Laboratory for Laser Energetics and Department of Electrical Engineering, 1994, pages 3578-3580.

EXAMINER

DATE CONSIDERED

a/20/03

* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.